## Small, Patricia

From:

Wilson, Denise M. [Denise.Wilson@haynesboone.com]

Sent:

Tuesday, January 25, 2005 12:09-PM

To:

Small, Patricia

Cc:

ODell, David M.

Subject:

8. Application No. 10/771691عبلا

Importance: High

Ms. Small,

Per our telephone conversation, the following is Paragraphs [0001] and [0002] on pages 1 and 2 adding serial numbers and deleting text. As we discussed, four of these related applications were never filed and therefore, the text is being deleted.

Should you have any questions, please feel free to contact me. Thank you for your help in this matter.

Thank you and regards,

## Denise M. Wilson

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Haynes and Boone, LLP

[0001] This application is related to the following commonly-assigned U.S. Patent Applications, the entire disclosures of which are hereby incorporated herein by reference:

- "MULTI-SENSING LEVEL MRAM STRUCTURES," <u>Application No. 10/685,824</u> Atterney Docket No. 24061.24, filed October 13, 2003, having Wen Chin Lin and Denny D. Tang named as inventors.
- "MULTI-SENSING LEVEL MRAM STRUCTURE WITH DIFFERENT MAGNETO-RESISTANCE RATIOS," <u>Application No. 10/678,699</u> Attorney Docket No. 24061.32, filed October 3, 2003, having Wen Chin Lin and Denny D. Tang named as inventors.

[0002] This application is also related to the following commonly-assigned U.S. Patent Applications:

- \_\_\_\_\*MRAM CELL HAVING TUBULAR FREE LAYER AND METHOD OF MANUFACTURE THEREOF," Attorney Docket No. 24061.88, having Wen Chin Lin, Denny D. Tang and Li Shyue Lai named as inventors.
- "NON-ORTHOGONAL WRITE LINE STRUCTURE IN MRAM," <u>Application No. 10/827,079</u>, filed April 19, 2004 Attorney Docket No. 24061.90, having Wen Chin Lin, Denny D. Tang and Li-Shyue Lai named as inventors.
- "SEGMENTED MRAM MEMORY ARRAY, " <u>Application No. 10/780171</u>, filed February 16, 2004 Attorney Decket No. 24061.163, having Wen Chin Lin, Denny D. Tang and Li-Shyue Lai named as inventors.
- ◆ \_\_\_\_<del>"MULTILAYER STRUCTURE FOR CLADDING LAYER OF BIT LINES AND DIGIT LINES IN MRAM."</del>

1911/1091

Dooket No. 2003-0382, having Wen Chin Lin, Denny D. Tang, Yu Jen Wang and Chih0Huang Laid named as inventors.

- "WAFER BUMP REWORK PROCESS FOR RECOVERY WAFER QUALITY," Docket No. 2003-0465, having Hadio-Ping Chang and Yi-Chun Lu named as inventors.
- "LOW Re SILICIDE FORMATION UTILIZING SOLID PHASE EPITAXY," Decket No. 2003-1366, having Steve Ming Ting named as inventor.

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